THE POSSIBILITIES ARE INFINITE FUITSU

FUJITSU SEMICONDUCTOR NEW PRODUCTS

NP05-11439-1E

64 Mbit Mobile FCRAM[™] 1.8V, Burst Mode MB82DBS04163D-70L (Now developing)

■ FEATURES

- Asynchronous SRAM Interface
- Complies with Common Specifications for Mobile RAM (COSMORAM)
- Burst Mode Function (Consecutive Read/Write Operation through Synchronization of System Clocks)
- 8 Words Page Address Access Capability
- Byte Control with \overline{LB} , \overline{UB} pin
- Low Power Consumption
- Various Power Down Mode
 - Sleep
 - 8 Mbit Partial
 - 16 Mbit Partial
- Chip/Wafer Business
- 71pin Plastic FBGA Package for Engineering Sample ONLY

■ PRODUCT OPTIONS

Part Number		MB82DBS04163D
Speed Version		70L
Organization		4 M WORD × 16 BIT
Ambient Temperature		-30 °C to +85 °C
Junction Temperature		-30 °C to +90 °C
Supply Voltage		1.7 V to 1.95 V
Burst Frequency	RL = 6	83 MHz
CLK Access Time (Max.)	RL = 6	6 ns
Read/Write Cycle Time (Min.)		70 ns
Random Access Time (Max.)		70 ns
Page Address Access Time (Max.)		20 ns
Active Current (Max.)		T.B.D.
Standby Current (Max.)		T.B.D.
Power Down Current (Max.)	Sleep	10 µA